# JESTEK

JST3404

30V N-Channel Mosfet

FEATURES

- $R_{DS(ON)} \le 25m\Omega$ (18mΩ Typ.) @V_{GS}=10V

- $R_{DS(ON)} \le 40m\Omega$ (28mΩ Typ.) @V_{GS}=4.5V

APPLICATIONS

- PWM Applications
- Load Switch
- Power Management

SOT-23
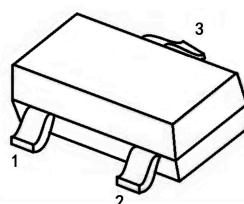
1. GATE
2. SOURCE
3. DRAIN

MARKING
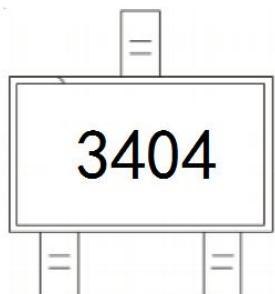
3404:Device Code

N-CHANNEL MOSFET
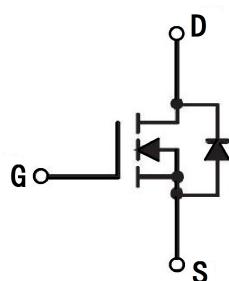
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_a = 25℃	5.8	A
		T_a = 100℃	4	
I_{DM}	Pulsed Drain Current [note1]		30	A
P_D	Power Dissipation	T_a= 25℃	1.5	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		85	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

## MOSFET ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 30V, V_{GS} = 0V, T_J = 25℃	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance note2	V_{GS} = 10V, I_D = 5A	-	18	25	mΩ
		V_{GS} = 4.5V, I_D = 4A	-	28	40	
g_{FS}	Forward Transconductance	V_{DS} = 5V, I_D = 5A	3	5.8	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz	-	560	-	pF
C_{oss}	Output Capacitance		-	125	-	pF
C_{rss}	Reverse Transfer Capacitance		-	90	-	pF
Q_g	Total Gate Charge	V_{DS} = 10V, I_D = 3.6A, V_{GS} = 5V	-	7	-	nC
Q_{gs}	Gate-Source Charge		-	1.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{GS} = 10V, V_{DS} = 15V, R_G = 2.5Ω, I_D = 5.5A	-	10	-	ns
t_r	Turn-On Rise Time		-	4	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	27	-	ns
t_f	Turn-Off Fall Time		-	5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5.8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 1.7A, T_J = 25℃	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%

TYPICAL PERFORMANCE CHARACTERISTICS

Power Capability

P_{tot} - Power (W)

$T_A=25^oC$

T_{mp} – Mounting Point Temp. (°C)

Current Capability

I_D - Drain Current (A)

$T_A=25^oC, V=10V$

T_{mp} – Mounting Point Temp. (°C)

Safe Operation Area

I_D - Drain Current (A)

Rds(on) Limit

100us
300us
1ms
10ms
100ms
1s
DC

$T_A=25^oC$

V_{DS} - Drain-Source Voltage (V)
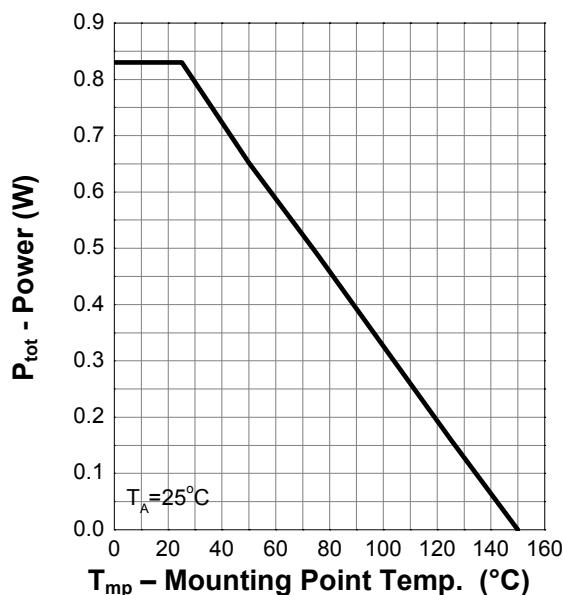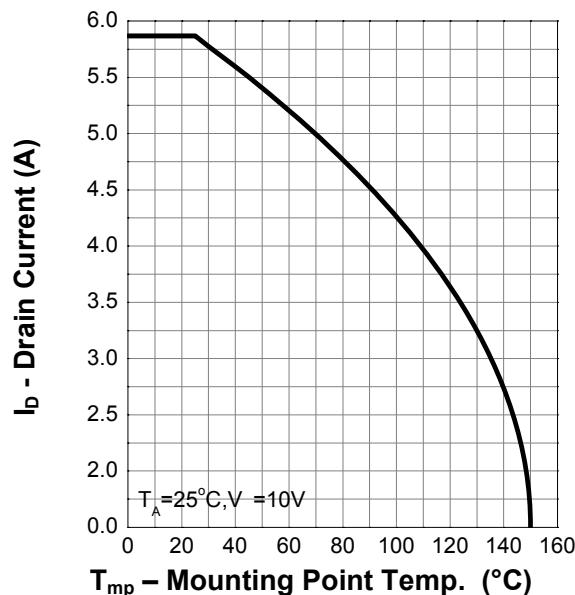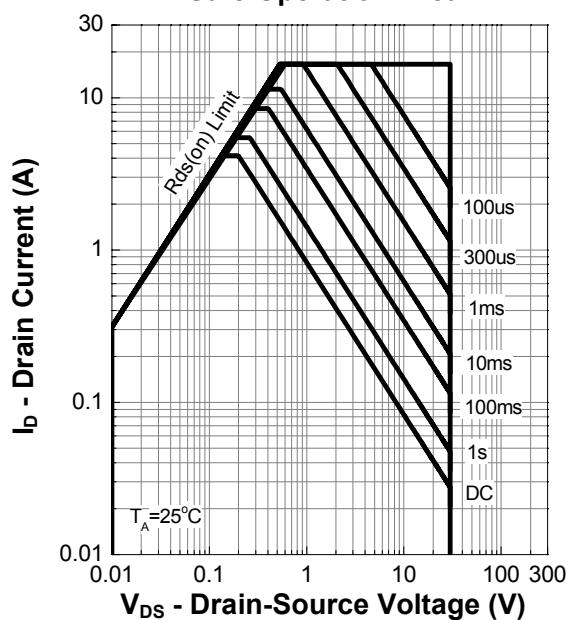
Transient Thermal Impedance

Normalized Transient Thermal Resistance

Duty = 0.5
0.2
0.1
0.05
0.02
0.01
Single Pulse

Mounted on 1in^2 pad
$R_{\theta JA}$: 150 °C/W

Square Wave Pulse Duration (sec)
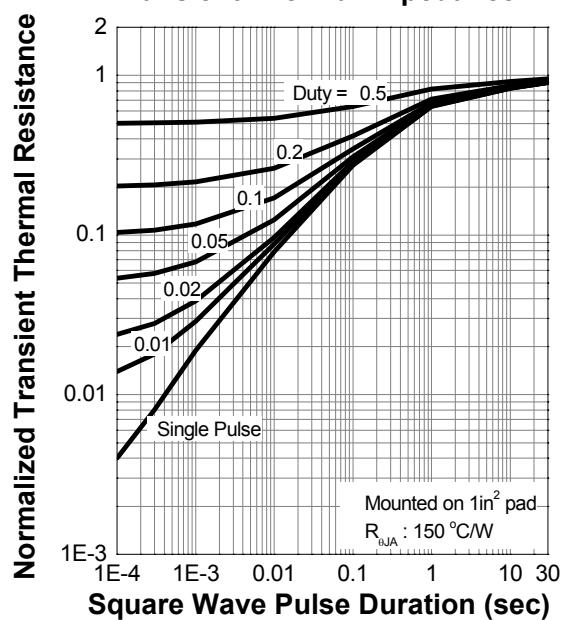
TYPICAL PERFORMANCE CHARACTERISTICS (cont.)

Output Characteristics

V_{GS} = 3, 4, 5, 6, 7, 8, 9, 10V

I_D - Drain Current (A) vs V_{DS} - Drain-Source Voltage (V)

2V

1V

On Resistance

$R_{DS(ON)}$ - On Resistance (mΩ) vs I_D - Drain Current (A)

V_{GS}=4.5V

V_{GS}=10V
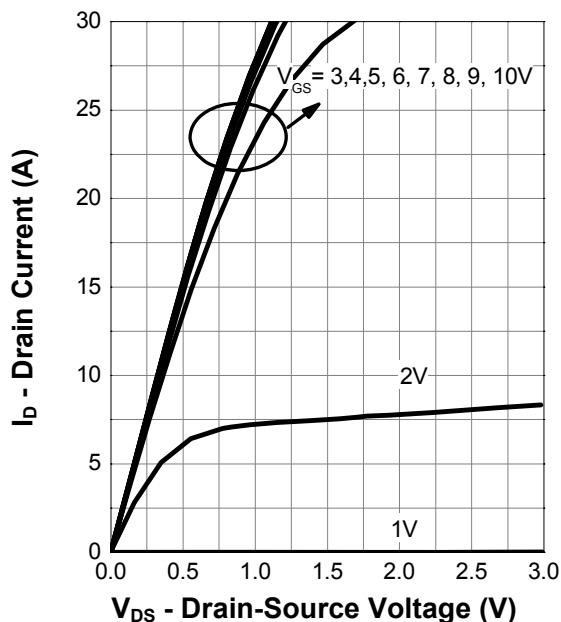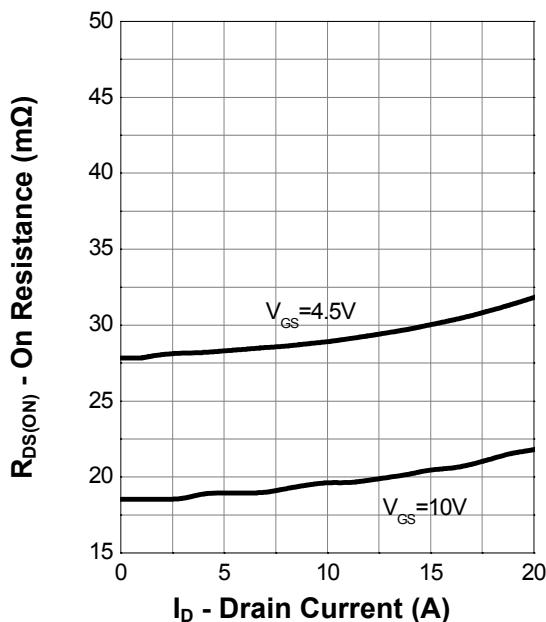
Transfer Characteristics

I_{DS}=5.8A

$R_{DS(ON)}$ - On Resistance (mΩ) vs V_{GS} - Gate-Source Voltage (V)

Normalized Threshold Voltage

I_{DS}=250μA

Normalized Threshold Voltage vs T_j - Junction Temperature (°C)
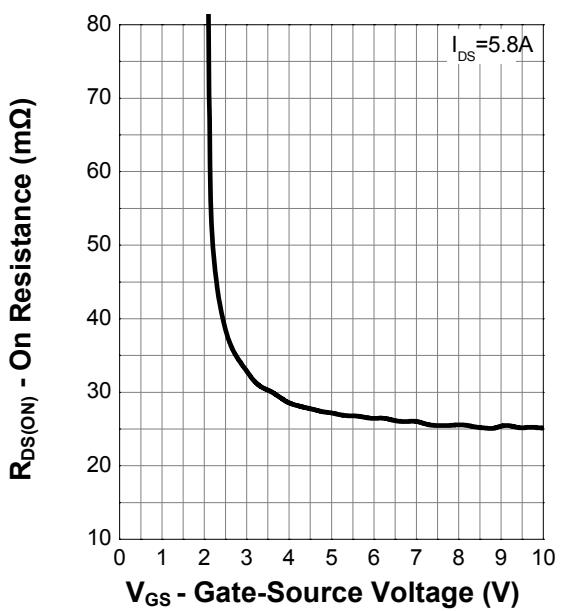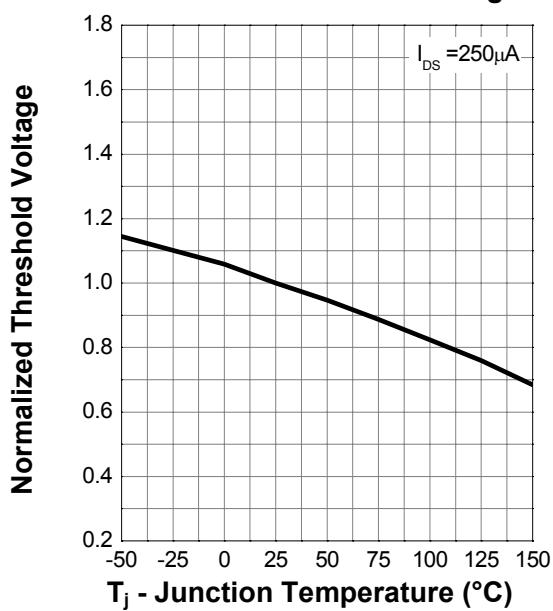
SOT-23 PACKAGE OUTLINE DRAWING
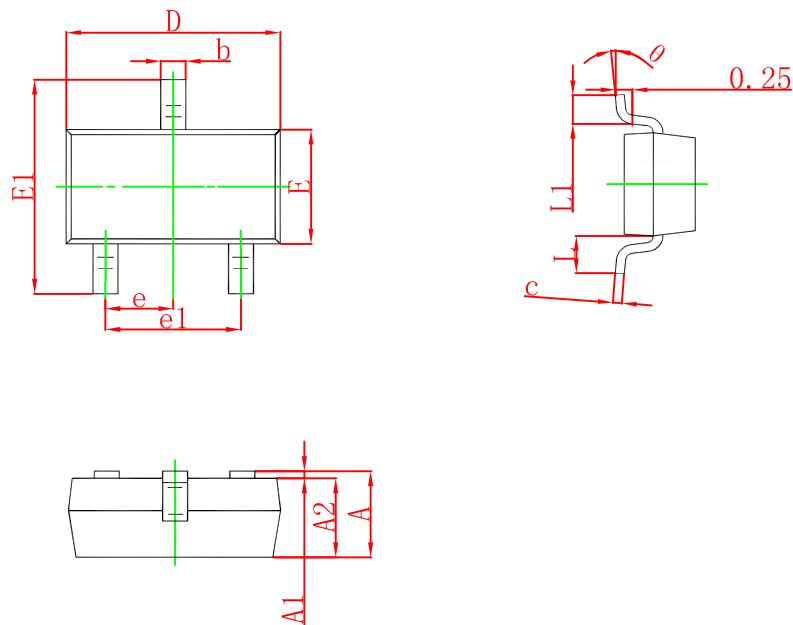
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°